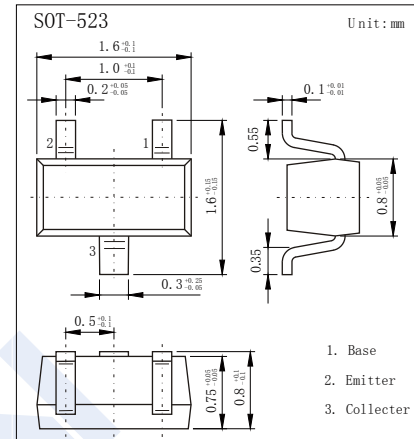


PNP Transistors

KX2001P

■ Features

- High Voltage Transistors
- Pb-Free Packages are Available



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-200	V
Collector - Emitter Voltage	V _{CEO}	-180	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-0.2	A
Collector Power Dissipation	P _c	0.15	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-200			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-180			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -120V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _c =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-50 mA, I _B =-5mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c = -50 mA, I _B =- 5mA			-1.0	
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _c = -10mA	100		250	
Transition frequency	f _T	V _{CE} = -5V, I _c = -10mA, f=30MHz	100		300	MHz

* Pulse Test: Pulse Width = 300 μs, Duty Cycle=2.0%.

■ Classification of hfe

Marking	21P
Range	100-250